9. (~~Amended~~) A device according to [any one of the preceding claims] claim 1, wherein additional titanium is formed on one or more of the surfaces that form the inner surface of a sealed cavity in the completed device.

13. (Amended) A method according to [any one of claims] claim 10 [to 12], wherein the hard layer is the first layer to be deposited on the glass and, subsequently, the second layer is deposited on top of the first layer.

14. (Amended) A method according to [any one of claims] claim 10 [to 13], wherein the layers are then subjected to two or more photolithography steps which firstly pattern the press contacts and wire bond pads in to the second layer and, secondly, pattern the conductors and electrodes in to the first layer.

15. (Amended) A method according to [any one of claims] claim 10 [to 14], wherein additional titanium is formed on one or more of the surfaces that form the inner surface of a sealed cavity in the completed device.

16. (Amended) A method according to [any one of claims] claim 10 [to 15], wherein the titanium acts as a getter to reduce the gas pressure in a sealed cavity after anodic bonding.

17. (Amended) A method according to [any one of claims] claim 10 [to 16], wherein the titanium acts as a getter to reduce the gas pressure in a sealed cavity after anodic bonding and this preferably occurs at approximately room temperature.

18. (Amended) A method according to [any one of claims] claim 10 [to 17], wherein the titanium acts as a getter to reduce the gas pressure in a sealed cavity after anodic bonding and during or after a heat treatment.

19. (Amended) A method according to [any one of] claim 10 [to 18], wherein the first layer is wet etched in an aqueous solution of ammonium hydroxide and hydrogen peroxide.

21. (Amended) A method according to [any one of claims] claim 10 [to 20], wherein the first and second layers are placed on the glass substrate instead of the semiconductor substrate to ensure that there is low stray capacitance within the device.